

200N6F3-VB-VB Datasheet

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0028
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0040
I_D (A)	210
Configuration	Single

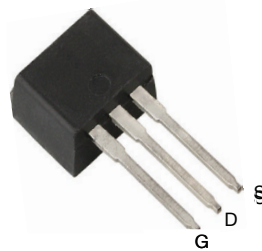
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

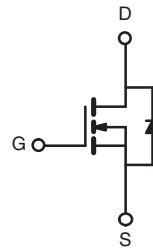


RoHS
COMPLIANT
HALOGEN
FREE

TO-262



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	210	A
	$T_C = 125^\circ\text{C}$		120 ^a	
Continuous Source Current (Diode Conduction) ^a		I_S	120 ^a	
Pulsed Drain Current ^b		I_{DM}	480	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	75	
Single Pulse Avalanche Energy		E_{AS}	281	mJ
Maximum Power Dissipation ^b	$T_C = 25^\circ\text{C}$	P_D	375	W
	$T_C = 125^\circ\text{C}$		125	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes

- Package limited.
- Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

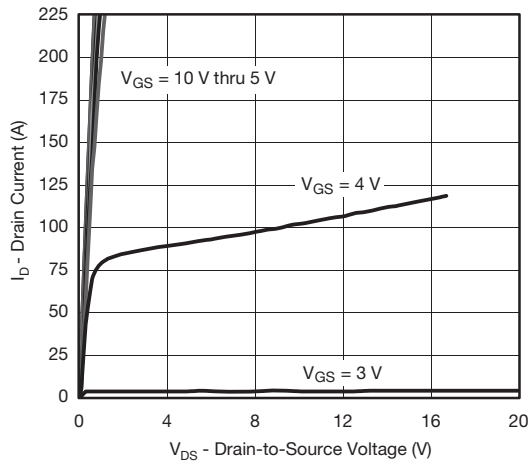
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	350	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.0028	-	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	0.0060	-	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	0.0080	-	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0040	-	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	109	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	7300	9125	pF
Output Capacitance	C _{oss}			-	935	1170	
Reverse Transfer Capacitance	C _{rss}			-	647	810	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 110 A	-	184	276	nC
Gate-Source Charge ^c	Q _{gs}			-	24.7	-	
Gate-Drain Charge ^c	Q _{gd}			-	50.4	-	
Gate Resistance	R _g	f = 1 MHz		0.5	1.1	1.6	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.27 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _g = 2.5 Ω		-	19	29	ns
Rise Time ^c	t _r			-	23	35	
Turn-Off Delay Time ^c	t _{d(off)}			-	83	125	
Fall Time ^c	t _f			-	35	53	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	480	A
Forward Voltage	V _{SD}	I _F = 100 A, V _{GS} = 0		-	0.9	1.5	V

Notes

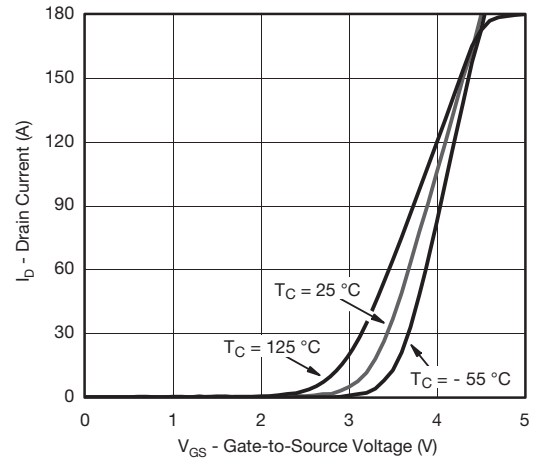
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

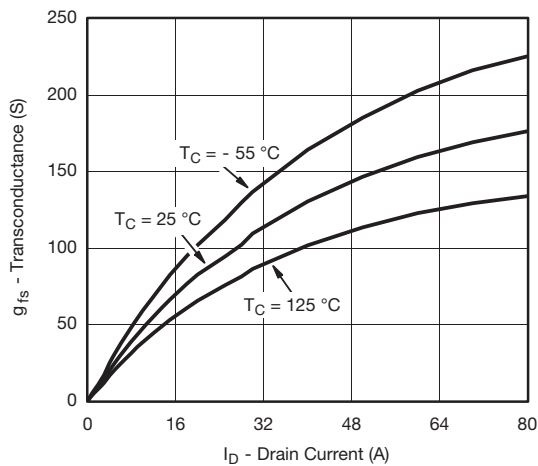
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



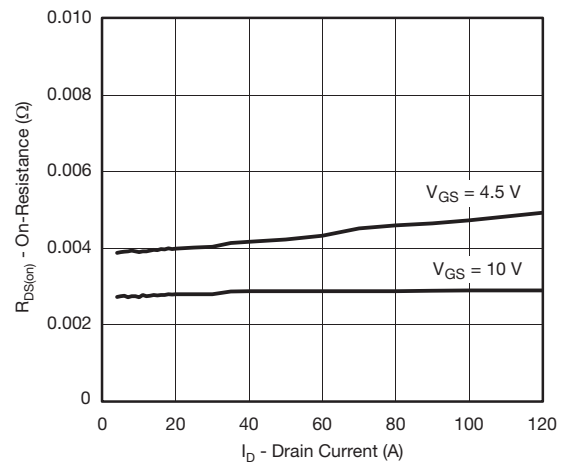
Output Characteristics



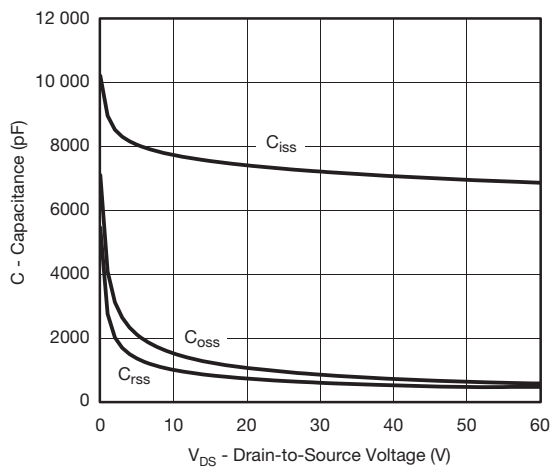
Transfer Characteristics



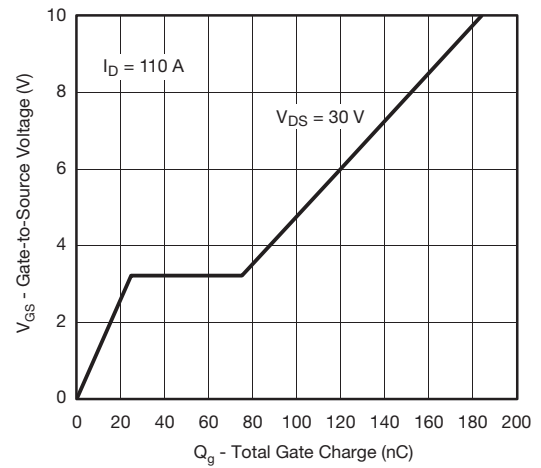
Transconductance



On-Resistance vs. Drain Current

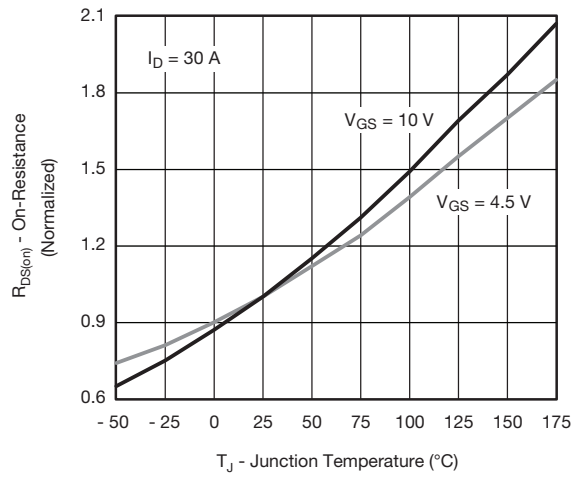


Capacitance

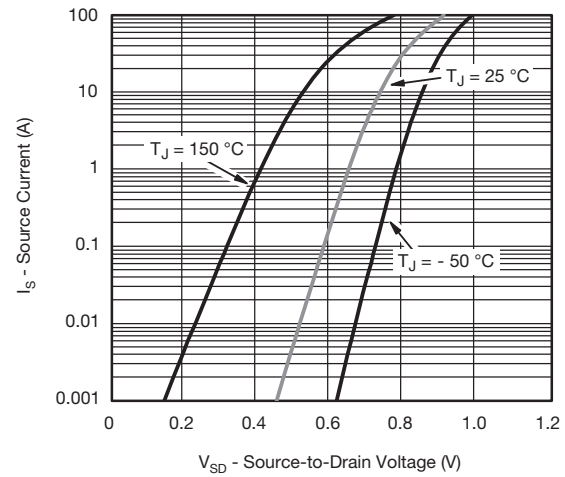


Gate Charge

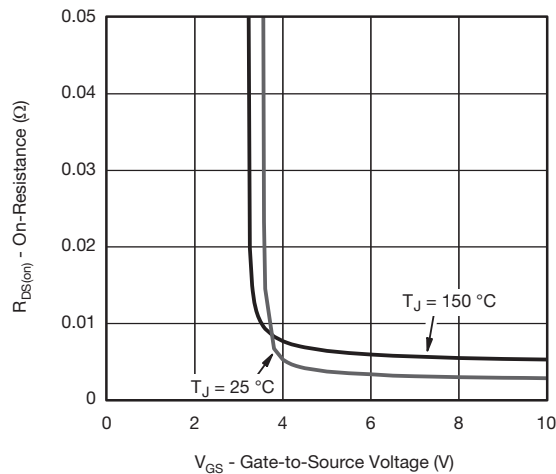
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



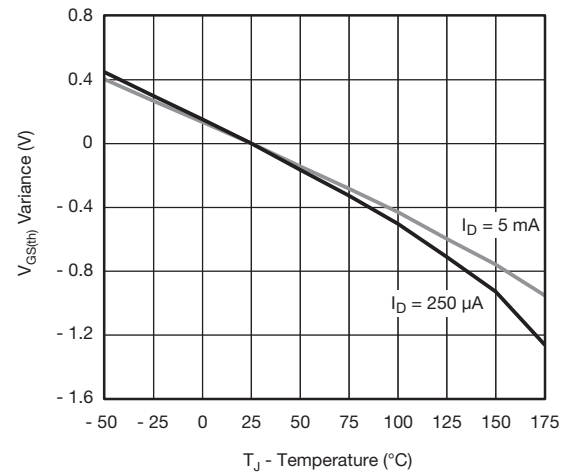
On-Resistance vs. Junction Temperature



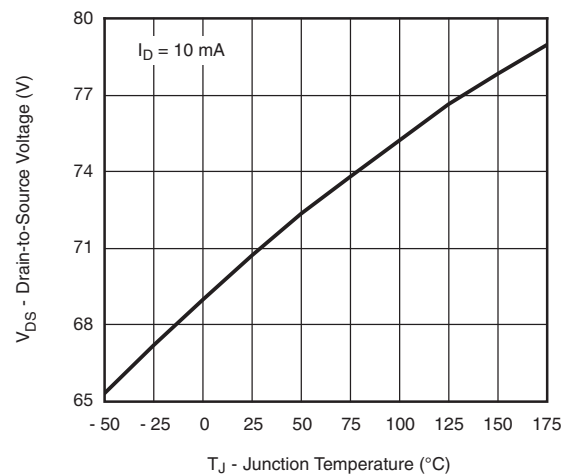
Source Drain Diode Forward Voltage



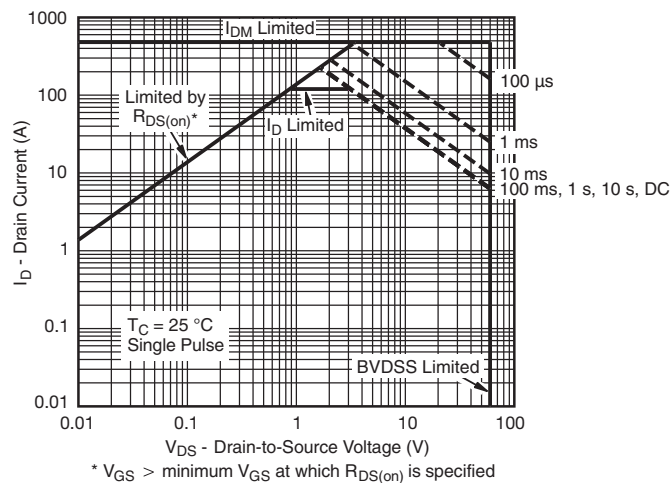
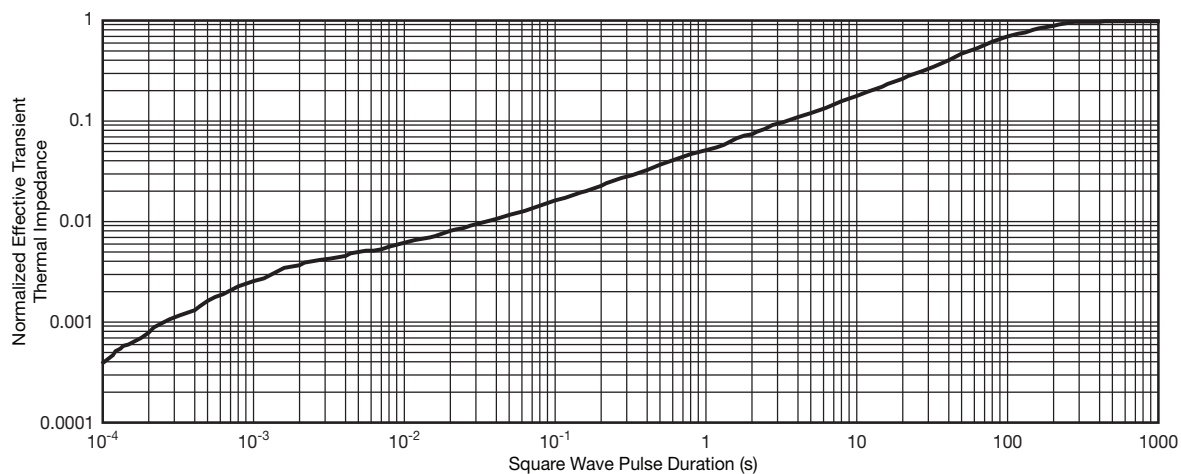
On-Resistance vs. Gate-to-Source Voltage

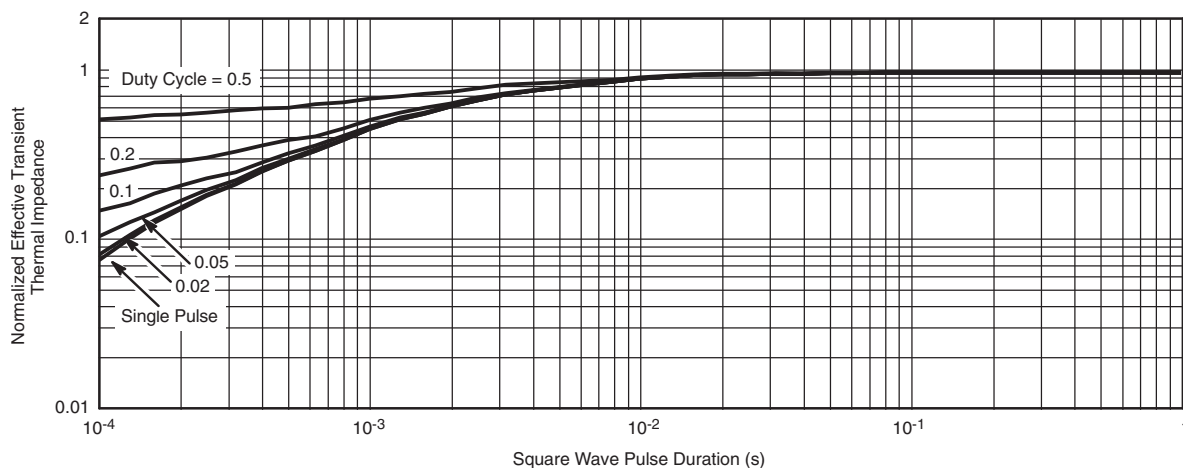


Threshold Voltage



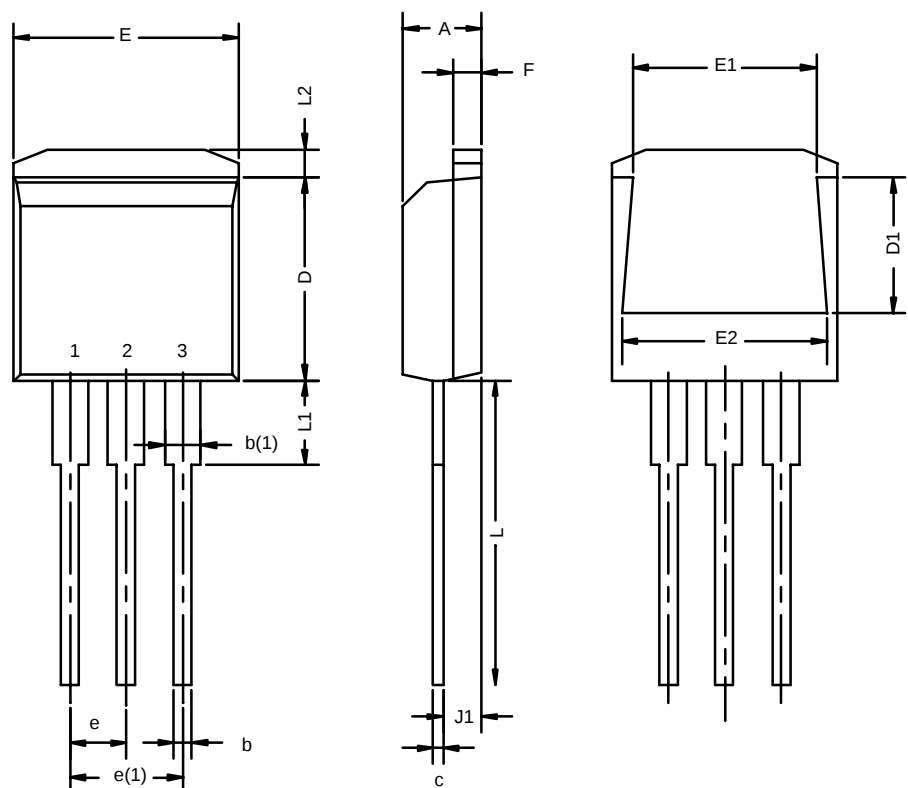
Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-262: 3-LEAD



Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	4.32	4.70	0.170	0.185
b	0.64	1.00	0.025	0.039
b(1)	1.14	1.40	0.045	0.055
c	0.36	0.50	0.014	0.020
D	8.64	9.65	0.340	0.380
D1	5.59	6.10	0.220	0.240
e	2.41	2.67	0.095	0.105
e(1)	4.95	5.33	0.195	0.210
E	10.03	10.41	0.395	0.410
E1	7.87	8.64	0.310	0.340
E2	9.02	9.53	0.355	0.375
F	1.14	1.40	0.045	0.055
J1	2.41	2.79	0.095	0.110
L	13.08	14.22	0.515	0.560
L1	-	3.81	-	0.150
L2	1.02	1.40	0.040	0.055
ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855				

*Use millimeters as the primary measurement

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